

2SD2453

Silicon NPN triple diffusion planar type

For high current transfer ratio and power amplification

■ Features

- High forward current transfer ratio h_{FE}
- Low collector-emitter saturation voltage $V_{CE(sat)}$

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 80 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 60 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 6 | V |
| Collector current | I_C | 2 | A |
| Peak collector current * | I_{CP} | 4 | A |
| Base current | I_B | 1 | A |
| Collector power dissipation | P_C | 10 | W |
| | | 1 | |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

Note) Non-repetitive peak collector current

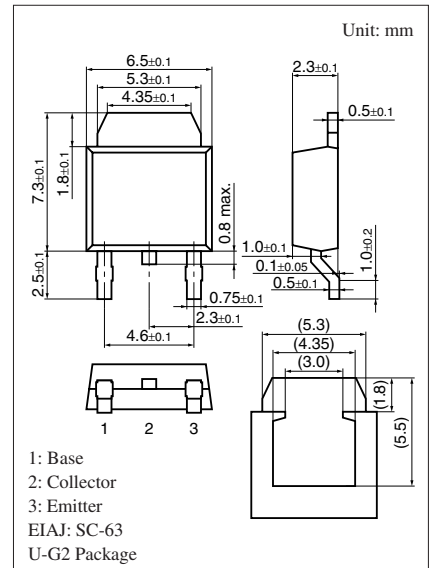
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|---------------|--|-----|-----|------|---------------|
| Collector-emitter voltage (Base open) | V_{CEO} | $I_C = 25 \text{ mA}, I_B = 0$ | 60 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 80 \text{ V}, I_E = 0$ | | | 100 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 40 \text{ V}, I_B = 0$ | | | 100 | μA |
| Emitter-base cutoff current (Collector open) | I_{EBO} | $V_{EB} = 6 \text{ V}, I_C = 0$ | | | 100 | μA |
| Forward current transfer ratio * | h_{FE} | $V_{CE} = 4 \text{ V}, I_C = 0.5 \text{ A}$ | 500 | | 2500 | — |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 2 \text{ A}, I_B = 0.05 \text{ A}$ | | | 1 | V |
| Transition frequency | f_T | $V_{CE} = 12 \text{ V}, I_C = 0.2 \text{ A}, f = 10 \text{ MHz}$ | | 50 | | MHz |

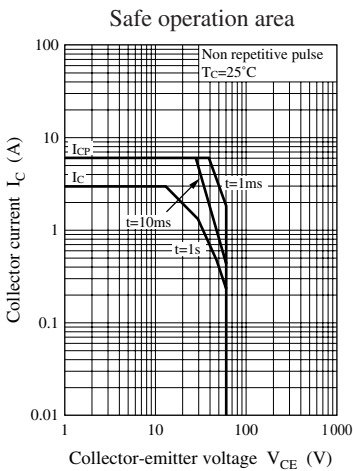
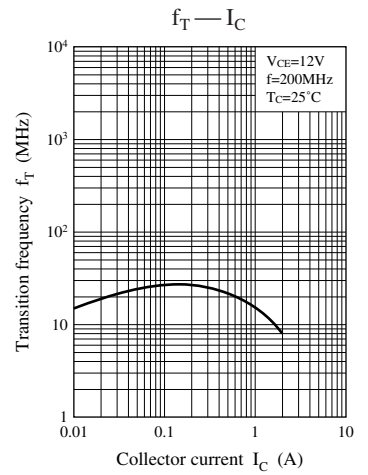
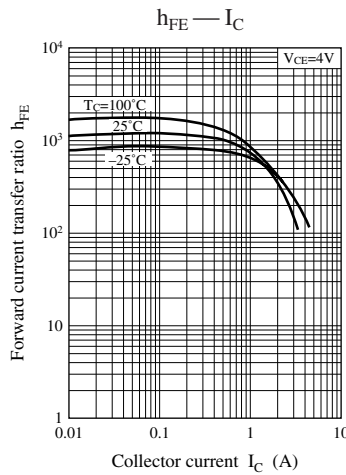
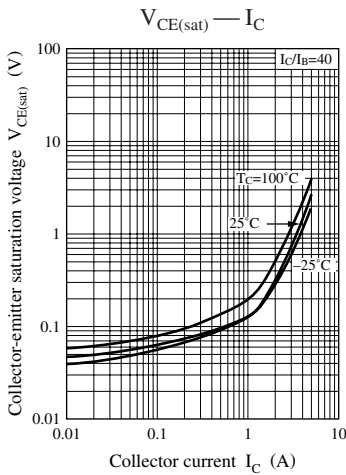
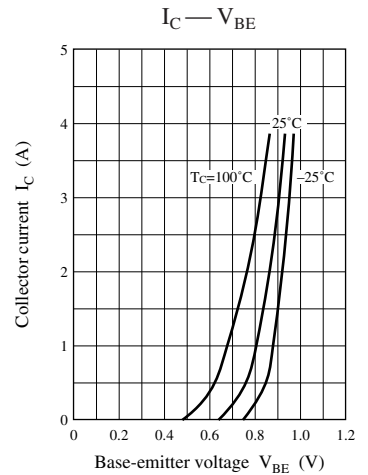
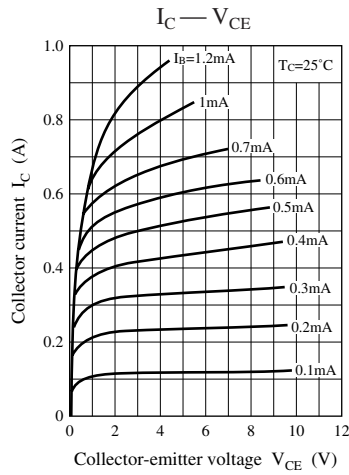
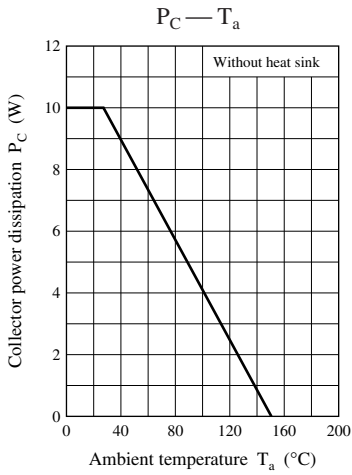
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

| Rank | Q | R | S |
|----------|-------------|-------------|--------------|
| h_{FE} | 500 to 1000 | 800 to 1500 | 1200 to 2500 |



Note) Self-supported type package is also prepared.



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